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PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

FXT751

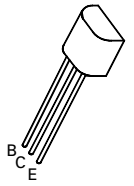
ISSUE 1 – FEB 94

FEATURES

* 60 Volt V_{CEO}
* 2 Amp continuous current
* P_{tot}= 1 Watt

APPLICATIONS

* Lamp, relay or solenoid drivers
* Audio circuits
* Replacement of TO126 and TO220 parts
  REFER TO ZTX751 FOR GRAPHS



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-2	A
Power Dissipation at T_{amb}=25°C	P_{tot}	1	W
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80			V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60			V	IC=-10mA, I_B=0*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-100μA, I_C=0
Collector Cut-Off Current	I_{CBO}			-0.1 -10	μA μA	V_{CB}=-60V, I_E=0 V_{CB}=-60V, T_{amb}=100°C
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	V_{EB}=-4V, I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.15 -0.28	-0.3 -0.5	V V	I_C=-1A, I_B=-100mA* I_C=-2A, I_B=-200mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.90	-1.25	V	I_C=-1A, I_B=-100mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1.0	V	IC=-1A, V_{CE}=-2V*
Static Forward Current Transfer Ratio	h_{FE}	70 100 80 40	200 200 170 150	300		I_C=-50mA, V_{CE}=-2V* I_C=-500mA, V_{CE}=-2V* I_C=-1A, V_{CE}=-2V* I_C=-2A, V_{CE}=-2V*
Transition Frequency	f_T	100	140		MHz	I_C=-100mA, V_{CE}=-5V f=100MHz
Output Capacitance	C_{obo}			30	pF	V_{CB}=-10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%